

## SILICON NPN SWITCHING TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR
- VERY HIGH SWITCHING SPEED

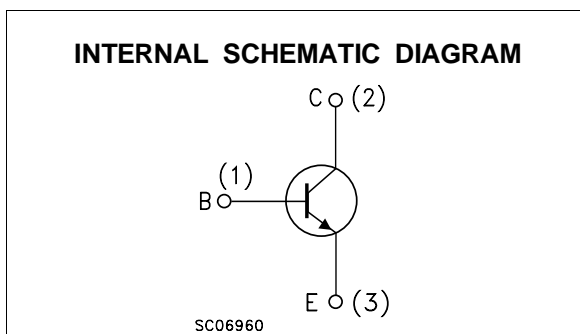
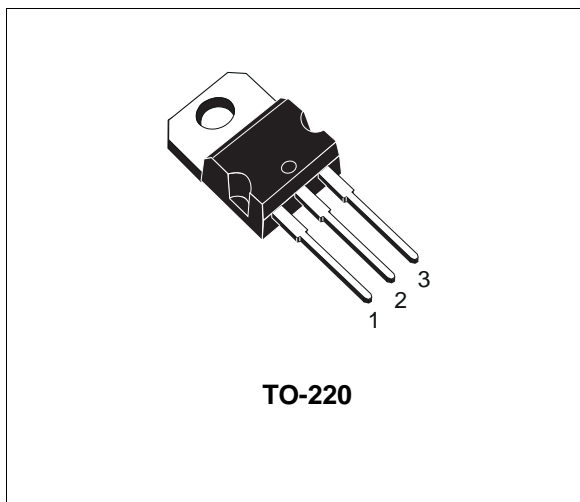
### APPLICATIONS:

- HORIZONTAL DEFLECTION FOR MONOCHROME TV

### DESCRIPTION

The BU406 is a silicon epitaxial planar NPN transistor in Jedec TO-220 plastic package.

It is a fast switching device for use in horizontal deflection output stages of large screens MTV receivers with 110° CRT.



### ABSOLUTE MAXIMUM RATINGS

| Symbol    | Parameter                                      | Value      | Unit |
|-----------|--|------------|------|
| $V_{CBO}$ | Collector-Base Voltage ( $I_E = 0$ )           | 400        | V    |
| $V_{CEV}$ | Collector-Emitter Voltage ( $V_{BE} = -1.5$ V) | 400        | V    |
| $V_{CEO}$ | Collector-Emitter Voltage ( $I_B = 0$ )        | 200        | V    |
| $V_{EBO}$ | Emitter-Base Voltage ( $I_C = 0$ )             | 6          | V    |
| $I_C$     | Collector Current                              | 7          | A    |
| $I_{CM}$  | Collector Peak Current (repetitive)            | 10         | A    |
| $I_{CM}$  | Collector Peak Current ( $t_p = 10$ ms)        | 15         | A    |
| $I_B$     | Base Current                                   | 4          | A    |
| $P_{tot}$ | Total Dissipation at $T_c \leq 25$ °C          | 60         | W    |
| $T_{stg}$ | Storage Temperature                            | -65 to 150 | °C   |
| $T_j$     | Max. Operating Junction Temperature            | 150        | °C   |

**THERMAL DATA**

|                       |                                     |     |      |      |
|-----------------------|-------------------------------------|-----|------|------|
| R <sub>thj-case</sub> | Thermal Resistance Junction-case    | Max | 2.08 | °C/W |
| R <sub>thj-amb</sub>  | Thermal Resistance Junction-ambient | Max | 70   | °C/W |

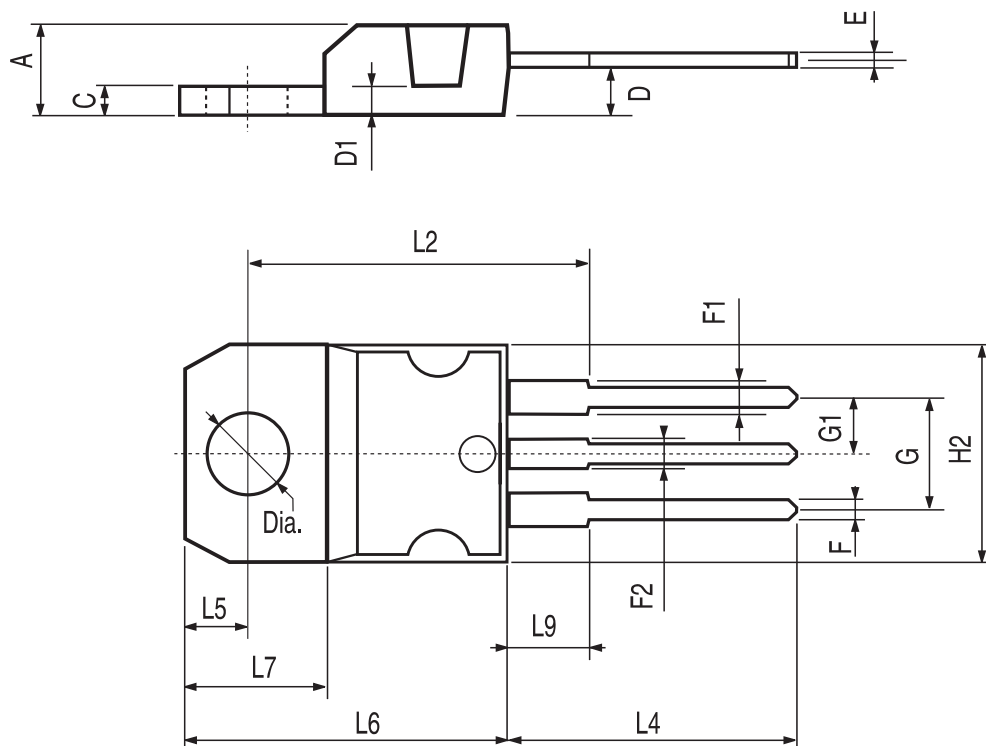
**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

| Symbol                | Parameter                                       | Test Conditions  | Min. | Typ. | Max.          | Unit           |
|-----------------------|---|--|------|------|---------------|----------------|
| I <sub>CES</sub>      | Collector Cut-off Current (V <sub>BE</sub> = 0) | V <sub>CE</sub> = 400 V<br>V <sub>CE</sub> = 250 V<br>V <sub>CE</sub> = 250 V<br>T <sub>case</sub> = 150°C |      |      | 5<br>100<br>1 | mA<br>μA<br>mA |
| I <sub>EBO</sub>      | Emitter Cut-off Current (I <sub>C</sub> = 0)    | V <sub>EB</sub> = 6 V  |      |      | 1             | mA             |
| V <sub>CE(sat)*</sub> | Collector-emitter Saturation Voltage            | I <sub>C</sub> = 5 A<br>I <sub>B</sub> = 0.5 A   |      |      | 1             | V              |
| V <sub>BE(sat)*</sub> | Base-emitter Saturation Voltage                 | I <sub>C</sub> = 5 A<br>I <sub>B</sub> = 0.5 A   |      |      | 1.2           | V              |
| f <sub>T</sub>        | Transition-Frequency                            | I <sub>C</sub> = 0.5 A<br>V <sub>CE</sub> = 10V  | 10   |      |               | MHz            |
| t <sub>off**</sub>    | Turn-off Time                                   | I <sub>C</sub> = 5 A<br>I <sub>Bend</sub> = 0.5 A  |      |      | 0.75          | μs             |
| I <sub>S/b</sub>      | Second Breakdown Collector Current              | V <sub>CE</sub> = 40 V<br>t = 10 ms  |      | 4    |               | A              |

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

## TO-220 MECHANICAL DATA

| DIM. | mm    |      |       | inch  |       |       |
|------|-------|------|-------|-------|-------|-------|
|      | MIN.  | TYP. | MAX.  | MIN.  | TYP.  | MAX.  |
| A    | 4.40  |      | 4.60  | 0.173 |       | 0.181 |
| C    | 1.23  |      | 1.32  | 0.048 |       | 0.051 |
| D    | 2.40  |      | 2.72  | 0.094 |       | 0.107 |
| D1   |       | 1.27 |       |       | 0.050 |       |
| E    | 0.49  |      | 0.70  | 0.019 |       | 0.027 |
| F    | 0.61  |      | 0.88  | 0.024 |       | 0.034 |
| F1   | 1.14  |      | 1.70  | 0.044 |       | 0.067 |
| F2   | 1.14  |      | 1.70  | 0.044 |       | 0.067 |
| G    | 4.95  |      | 5.15  | 0.194 |       | 0.203 |
| G1   | 2.4   |      | 2.7   | 0.094 |       | 0.106 |
| H2   | 10.0  |      | 10.40 | 0.393 |       | 0.409 |
| L2   |       | 16.4 |       |       | 0.645 |       |
| L4   | 13.0  |      | 14.0  | 0.511 |       | 0.551 |
| L5   | 2.65  |      | 2.95  | 0.104 |       | 0.116 |
| L6   | 15.25 |      | 15.75 | 0.600 |       | 0.620 |
| L7   | 6.2   |      | 6.6   | 0.244 |       | 0.260 |
| L9   | 3.5   |      | 3.93  | 0.137 |       | 0.154 |
| DIA. | 3.75  |      | 3.85  | 0.147 |       | 0.151 |



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